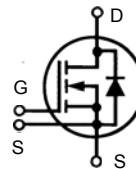


HiPerFET™ Power MOSFETs

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

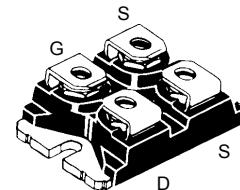
IXFN 22N120

$V_{DSS} = 1200V$
 $I_{D25} = 22A$
 $R_{DS(on)} = 0.55\Omega$
 $t_{rr} \leq 300ns$



Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V	
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$; $R_{GS} = 1 M\Omega$	1200	V	
V_{GS}	Continuous	± 30	V	
V_{GSM}	Transient	± 40	V	
I_{D25}	$T_c = 25^\circ C$, Chip capability	22	A	
I_{DM}	$T_c = 25^\circ C$, pulse width limited by T_{JM}	88	A	
I_{AR}	$T_c = 25^\circ C$	22	A	
E_{AR}	$T_c = 25^\circ C$	30	mJ	
dv/dt	$I_S \leq I_{DM}$, $dI/dt \leq 100 A/\mu s$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$, $R_G = 2 \Omega$	5	V/ns	
P_D	$T_c = 25^\circ C$	625	W	
T_J		-55 ... +150	$^\circ C$	
T_{JM}		150	$^\circ C$	
T_{stg}		-55 ... +150	$^\circ C$	
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 mA$	t = 1 min t = 1 s	2500 3000	V~ V~
M_d	Mounting torque Terminal connection torque		1.5/13 Nm/lb.in. 1.5/13 Nm/lb.in.	
Weight		30	g	

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source
TAB = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard packages
- miniBLOC, with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

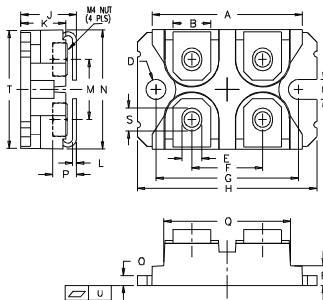
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ C$, unless otherwise specified)	min.	typ.
V_{DSS}	$V_{GS} = 0 V$, $I_D = 3 mA$	1200		V
$V_{GH(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 mA$	3.0		V
I_{GSS}	$V_{GS} = \pm 30 V_{DC}$, $V_{DS} = 0$		± 200	nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$	$T_J = 25^\circ C$ $T_J = 125^\circ C$		$50 \mu A$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu s$, duty cycle $d \leq 2\%$		0.55	Ω

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
g_{fs}	$V_{DS} = 20 \text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	15	26	S
C_{iss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	8100	pF	
C_{oss}		650	pF	
C_{rss}		200	pF	
$t_{d(on)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1 \Omega$ (External),	25	ns	
t_r		45	ns	
$t_{d(off)}$		76	ns	
t_f		28	ns	
$Q_{g(on)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$	210	nC	
Q_{gs}		38	nC	
Q_{gd}		99	nC	
R_{thJC}			0.20	K/W
R_{thCK}			0.05	K/W

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
I_s	$V_{GS} = 0 \text{ V}$		22	A
I_{SM}	Repetitive; pulse width limited by T_{JM}		88	A
V_{SD}	$I_F = I_S, V_{GS} = 0 \text{ V}$, Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$		1.3	V
t_{rr}	$I_F = I_S, -di/dt = 100 \text{ A}/\mu\text{s}, V_R = 100 \text{ V}$	180	300	ns
Q_{RM}		1.4	μC	
I_{RM}		8	A	